



DMG3404L

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
001/	$25m\Omega$ @ $V_{GS} = 10V$	5.8A
30V	35mΩ @ V _{GS} = 4.5V	4.8A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

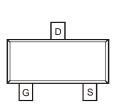
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ³
- Terminals Connections: See Diagram Below
- Weight: 0.009138 grams (Approximate)

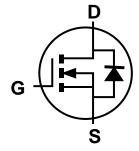
SOT23



Top View



Top View Pin Configuration



Equivalent Circuit

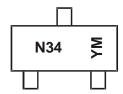
Ordering Information (Note 4)

Part Number	Case	Packaging
DMG3404L-7	SOT23	3000/Tape & Reel
DMG3404L-13	SOT23	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



N34 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Year	2012	2	2013	2014		2015	2016		2017	2018		2019
Code	Z		Α	В		С	D		Е	F		G
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

January 2016

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	30	V		
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	4.2 3.5	А
Continuous Drain Current (Note 6) V _{GS} = 10V	I _D	5.8 4.9	А		
Pulsed Drain Current (Pulse Width ≤10µS, Duty	Cycle ≤1%)	I _{DM}	30	Α	

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.78	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	164	°C/W
Power Dissipation (Note 6)	P _D	1.33	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	96	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

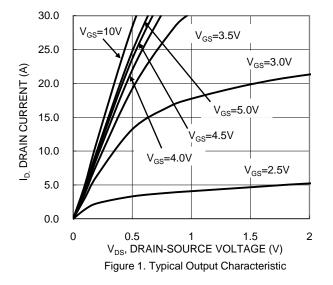
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1.0	1.5	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	_	_	21	25	~ 0	$V_{GS} = 10V, I_D = 5.8A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	24	35	mΩ	$V_{GS} = 4.5V, I_D = 4.8A$	
Diode Forward Voltage	V_{SD}	_	0.75	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	641	_	pF	451/1/	
Output Capacitance	Coss	_	66	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	51	_	pF	1 = 1.0WH 12	
Gate Resistance	Rg	_	2.2	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qq	_	13.2	_	nC		
Gate-Source Charge	Q _{gs}	_	1.7	_	nC	$V_{GS} = 10V, V_{DS} = 15V, I_{D} = 5.8$	
Gate-Drain Charge	Q _{qd}	_	2.2	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	3.3	_	ns		
Turn-On Rise Time	t _R	_	4.4	_	ns	$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	22	_	ns	$R_L = 1.25\Omega$, $R_g = 3\Omega$	
Turn-Off Fall Time	t _F	_	5.2	_	ns	1	

Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.





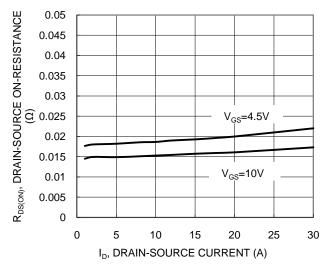


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

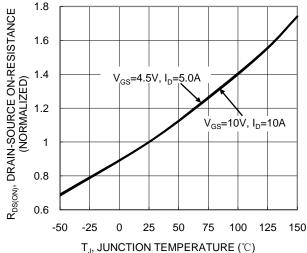
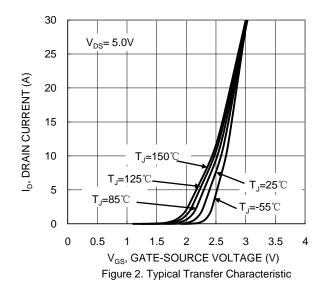


Figure 5. On-Resistance Variation with Temperature



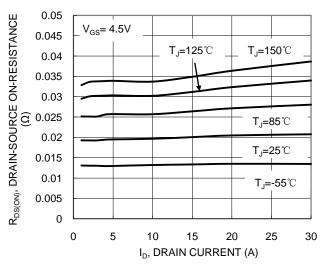


Figure 4. Typical On-Resistance vs. Drain Current and Temperature

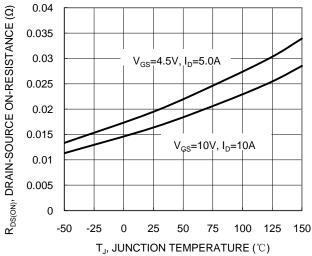
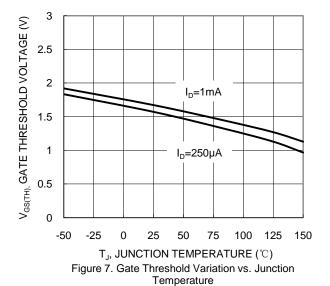
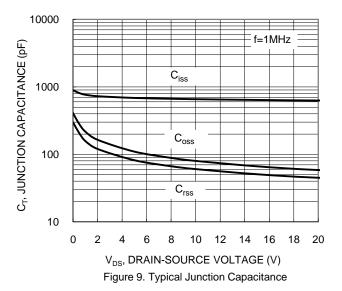


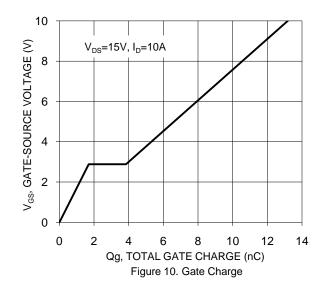
Figure 6. On-Resistance Variation with Temperature

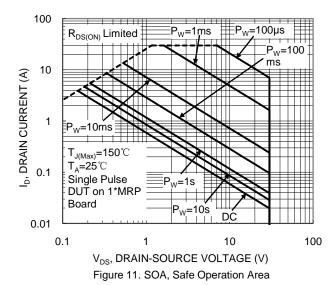




30 Is, SOURCE CURRENT (A) 25 20 15 V_{GS} =0V, T_A =25 $^{\circ}$ C 10 5 0 0 0.2 0.4 0.6 8.0 1.2 V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 8. Diode Forward Voltage vs. Current









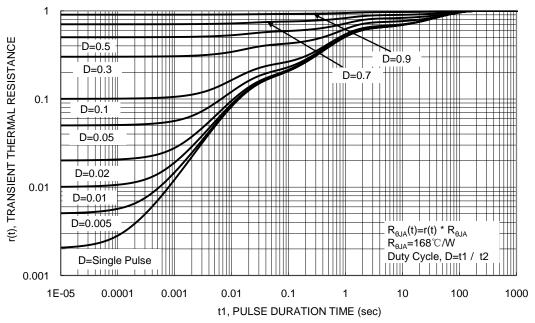
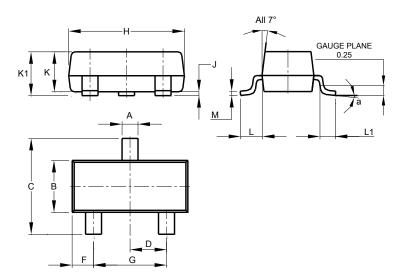


Figure 12. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT23



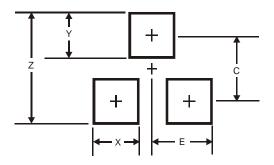
SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
а	8°						
All Dimensions in mm							



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT23



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35

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